



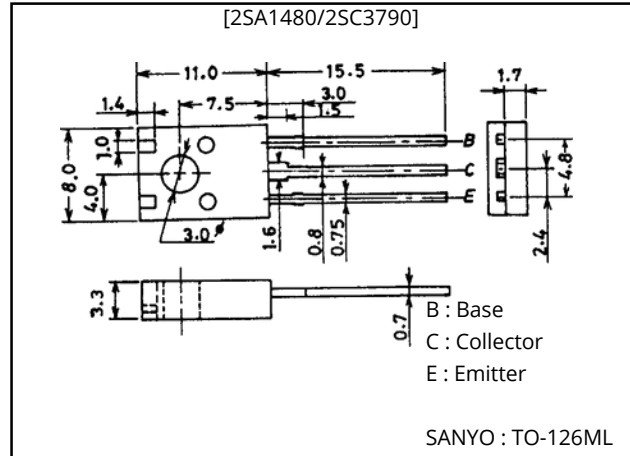
2SA1480/2SC3790

High-Definiton CRT Display Video Output Applications

Features

- High breakdown voltage ($C_{VEO} \geq 300V$), unit:mm · Small reverse transfer capacitance and excellent high frequency characteristic
- Cre=1.8pF (NPN), 2.3pF (PNP).
- Adoption of MBIT process.

Package Dimensions



() : 2SA1480

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB}		(-)300	V
Collector-to-Emitter Voltage	V_{CE}		(-)300	V
Emitter-to-Base Voltage	V_{EB}		(-)5	V
Collector Current	I_C		(-)100	mA
Peak Collector Current	I_{CP}		(-)200	mA
Collector Dissipation	P_C	$T_c = 25^\circ C$	1.5	W
Junction Temperature	T_j		150	$^\circ$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CO}	$V_{CB} = (-)200V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EO}	$V_{EB} = (-)4V, I_C = 0$	40*		(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)10mA$		150	320*	μA
Gain-Bandwidth Product	f_T	$V_{CE} = (-)30V, I_C = (-)10mA$		2.6		z pF
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		(3.1)		pF
Reverse Transfer Capacitance	C_{re}			1.8		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$				(-)0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$				(-)1.0	V
Collector-to-Base Breakdown Voltage	V_{CBR}		(-)300			V
Collector-to-Emitter Breakdown Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$	(-)300			V
Emitter-to-Base Breakdown Voltage	V_{EBR}		(-)5			V

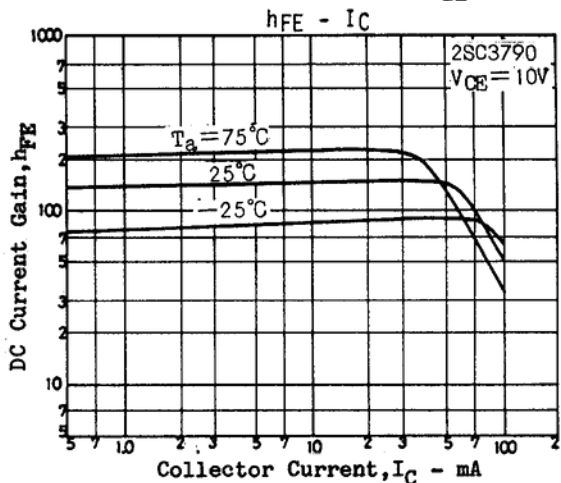
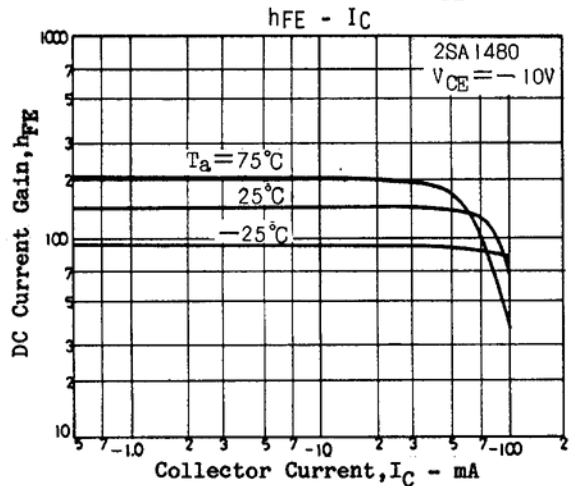
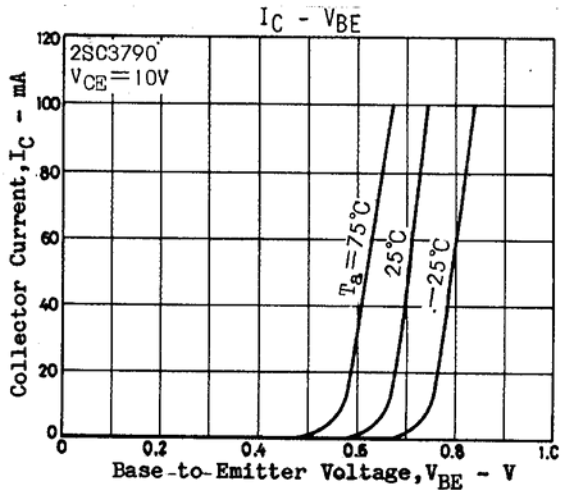
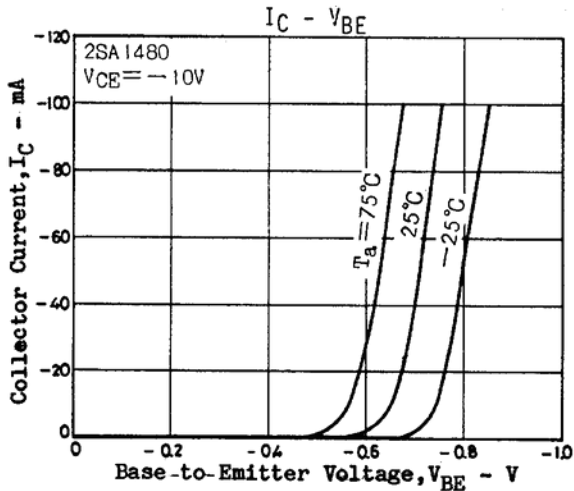
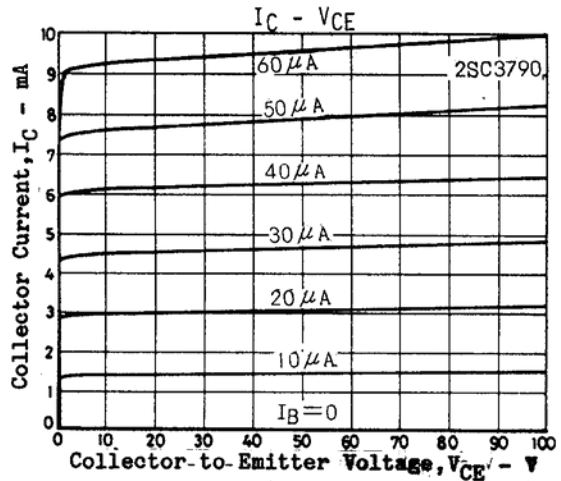
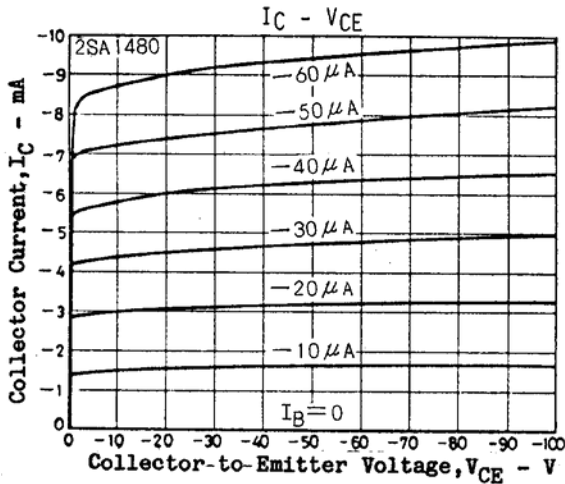
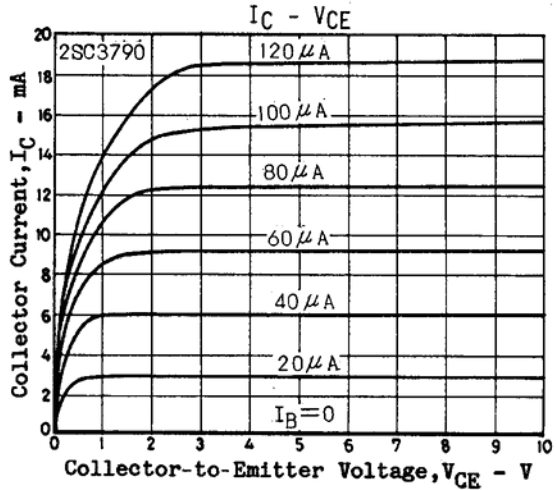
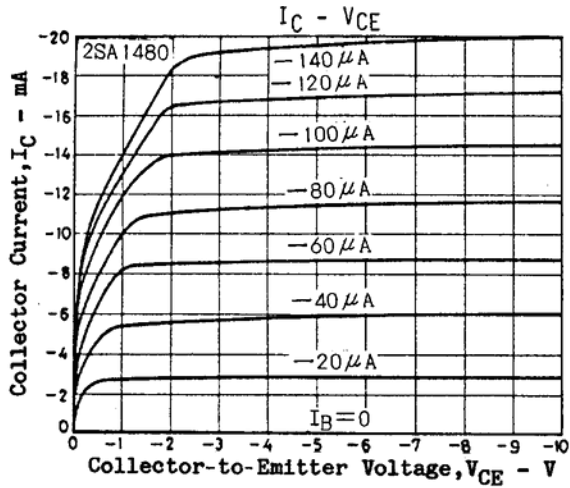
* : The 2SA1480/2SC3790 are classified by 10mA, $I_C = (-)20mA, I_B = (-)2mA$

40	C	80	60	D	120	100	E	300	F	160	320	G
$(BR) V_{CB} = (-)200V, I_E = 0$ $(BR) V_{EB} = (-)4V, I_C = 0$ $(BR) V_{CE} = (-)10V, I_C = (-)10mA$ $(BR) V_{CE} = (-)30V, I_C = (-)10mA$ $(BR) V_{CB} = (-)30V, f = 1MHz$ $(BR) V_{CE} = (-)30V, I_C = (-)10mA, I_B = (-)2mA$ $(BR) V_{EB} = (-)10V, I_C = 0$												

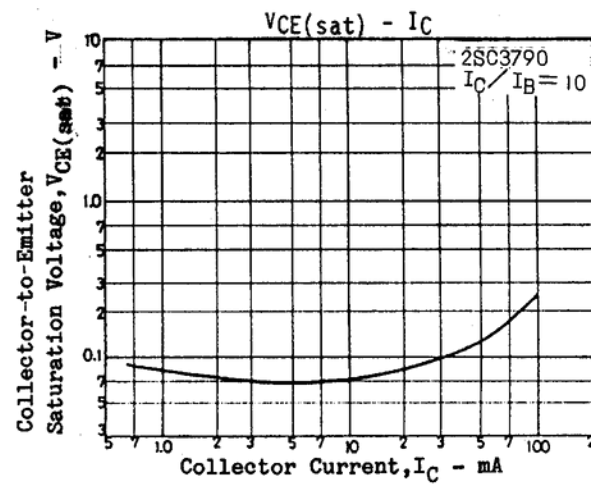
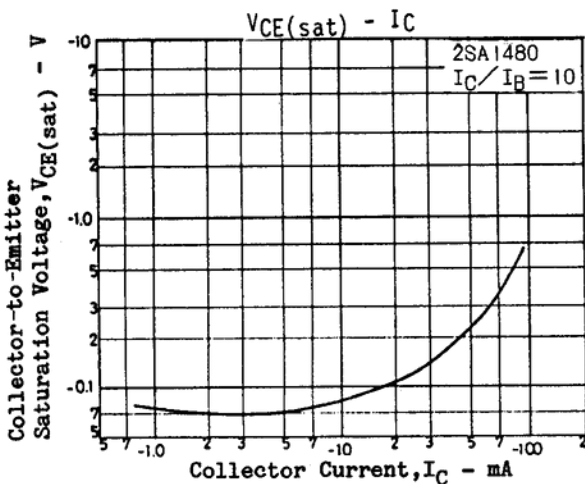
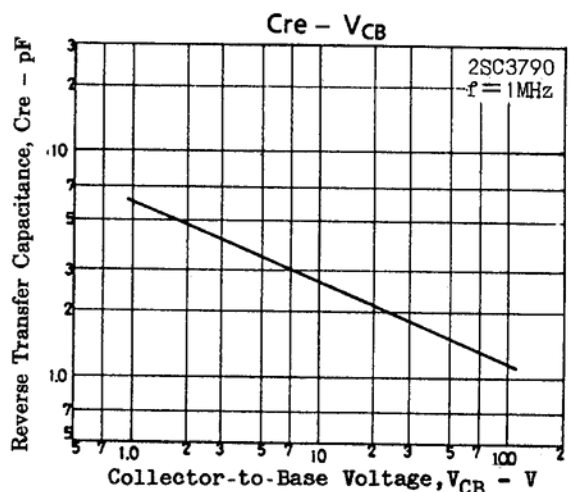
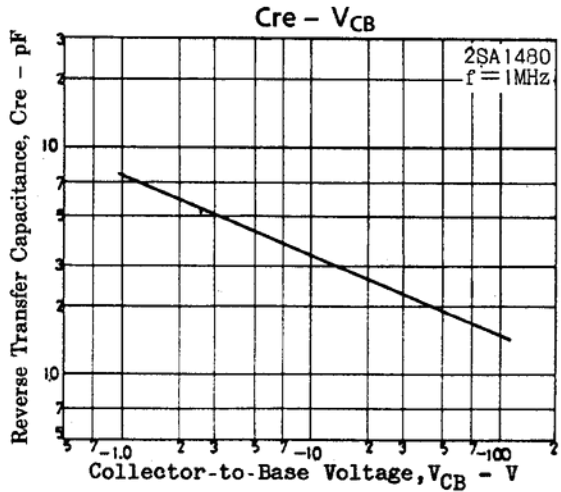
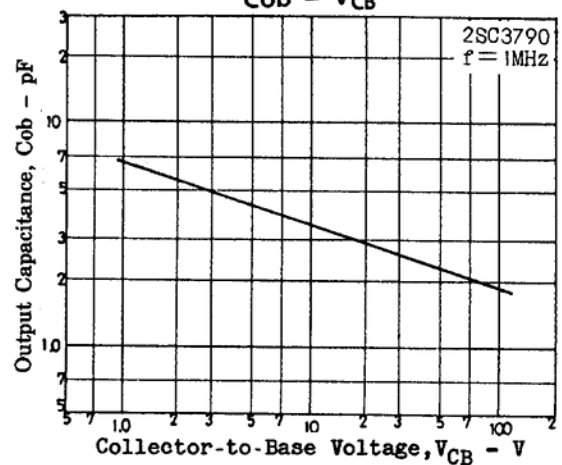
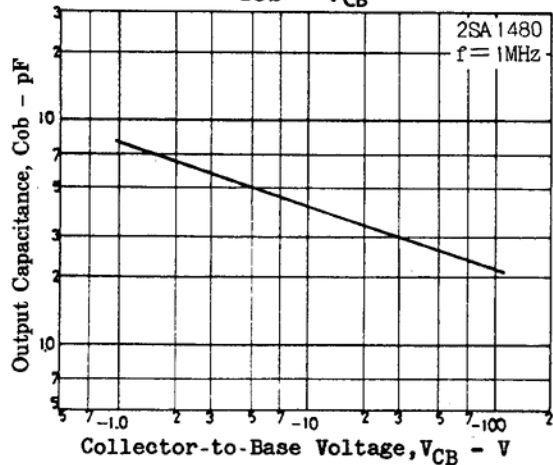
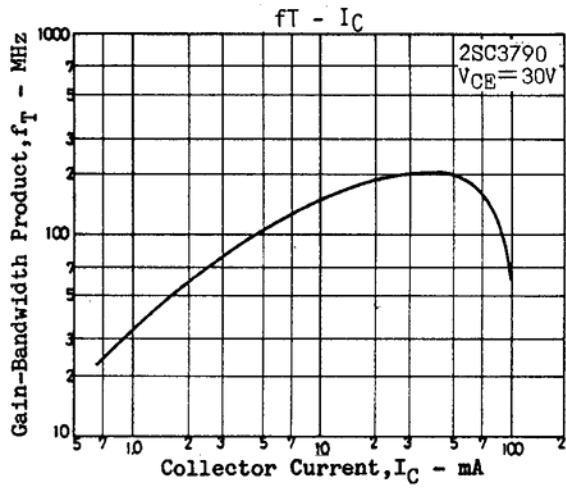
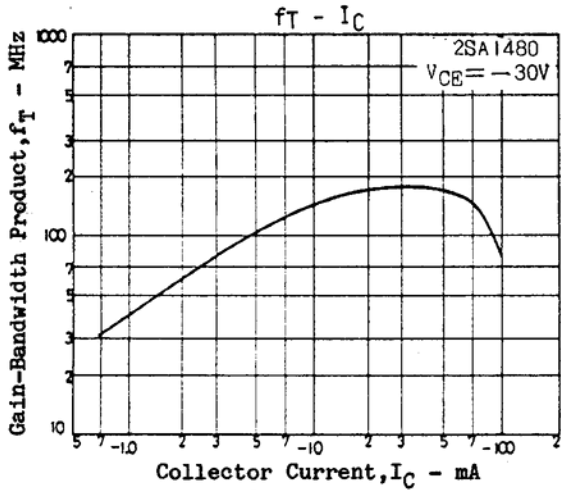
SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

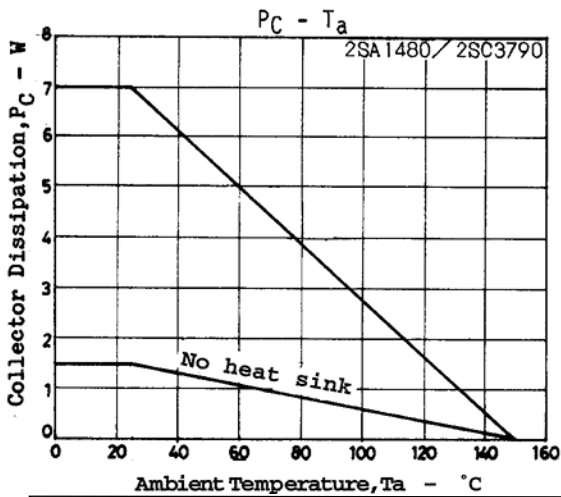
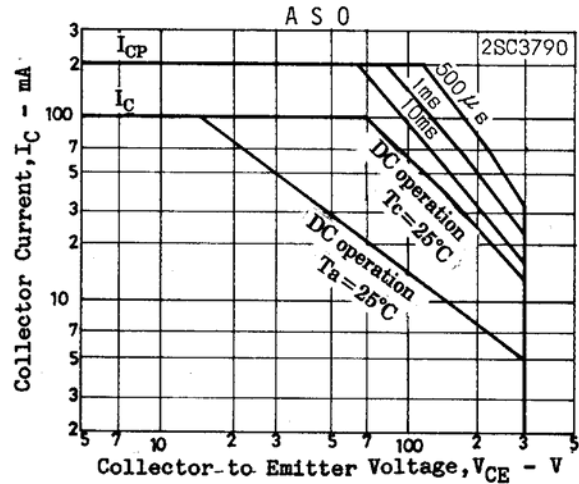
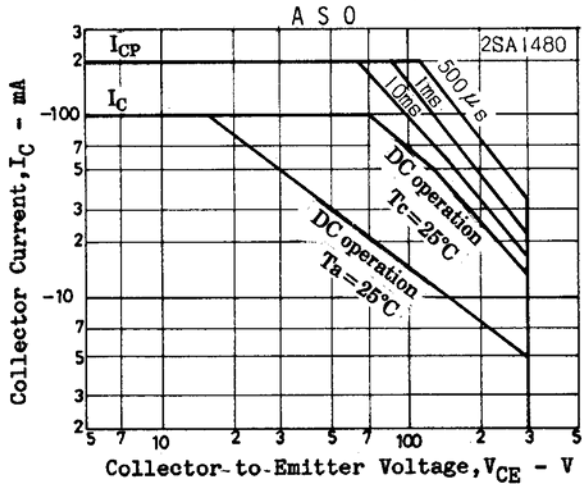
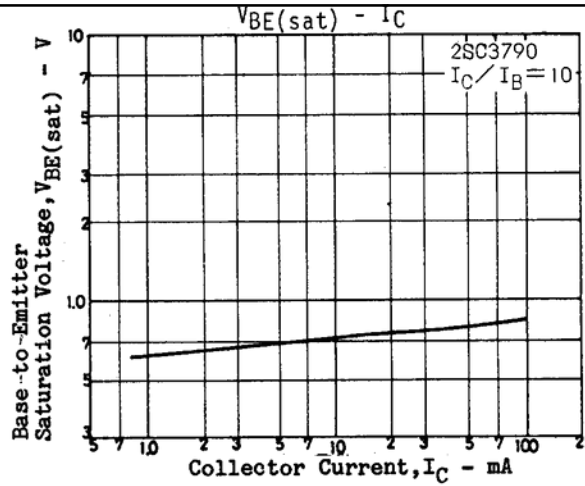
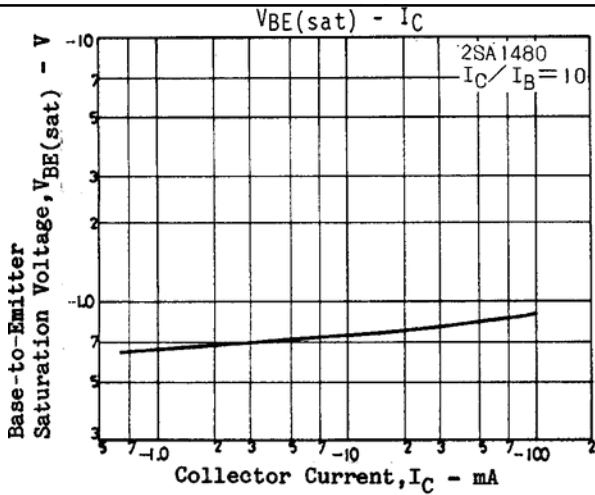
2SA1480/2SC3790



2SA1480/2SC3790



2SA1480/2SC3790



None of the products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.

Anyone purchasing any products described or contained herein for an above-mentioned use shall:

① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:

② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.

Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of July, 1998. Specifications and information herein are subject to change without notice.